File   View   Edit   Tools   Window   Help

Drafts
  IS&R:
Pending
Active
  L1: (2257620) current
  L2: (4328796) increase or increases or
  L3: (134855) erasing or erase or erase
  L4: (907652) negative
  L5: (994352) pulse or pulses
  L6: (56746) word adj (line or lines)
  L7: (7904) wordline or wordlines
  L8: (478514) drain
  L9: (2494851) source
  L10: (7170) bitline or bitlines
  L11: (65188) bit adj (line or lines)
  L12: (34164) control adj gate
  L13: (2912) 4 adj5 (6 or 7 or 12)
  L14: (38190) 5 adj5 (8 or 9 or 10 or 1
  L15: (5758) 14 with 1
  L16: (220699) 1 near9 2
  L17: (219) 14 with 16
  L18: (2) 17 same 13 same 3
  L19: (3) 14 same 16 same 13 same 3
  L20: (4584) 4 near9 (6 or 7 or 12)
  L21: (79706) 5 near9 (8 or 9 or 10 or
  L22: (4) 20 same 16 same 21 same 3
  L23: (75) 20 same 21 same 3
  L24: (14) 23 and 16
Failed

Search   Ins   Browse   Count

DBs   U   Plurals

Default operator: Highlight all hit terms initially

23 and 16

BRS form   IS&R form   Image   Text

	U	1	Document ID	Issue Dat	Pages	Title	Current OR	Curre
1			US 20040223	20041111	38	Electrically programmab	365/185.22	365/1
2			US 20040214	20041028	127	Rail stack array of cha	438/149	
3			US 20040206	20041021	126	Dense arrays and charge	257/296	
4			US 20040184	20040923	9	Non-volatile memory era	365/185.18	
5			US 20040012	20040122	10	Non-volatile memory era	365/185.18	
6			US 20030169	20030911	44	Semiconductor memory de	365/185.21	
7			US 20020028	20020307	151	Dense arrays and charge	438/149	257/E
8			US 6807101	20041019	42	Semiconductor memory de	365/185.21	365/1
9			US 6781880	20040824	9	Non-volatile memory era	365/185.18	365/1

Hits   Details   HTML

Ready   NUM